SIEMENS

ILCT6
DUAL PHOTOTRANSISTOR OPTOCOUPLER

FEATURES

- **Current Transfer Ratio, 50% Typical**
- **Leakage Current, 1 nA Typ.**
- **Two Isolated Channels Per Package**
- **Direct Replacement for MCT6**
- **Underwriters Lab File #E52744**
- **VDE 0884 Available with Option1**

DESCRIPTION

The ILCT6 is a two channel opto isolator for high density applications. Each channel consists of an optically coupled pair with a gallium arsenide infrared LED and a silicon NPN phototransistor. Signal information, including a DC level, can be transmitted by the device while maintaining a high degree of electrical isolation between input and output.

The ILCT6 is especially designed for driving medium-speed logic, where it may be used to eliminate troublesome ground loop and noise problems. It can also be used to replace relays and transformers in many digital interface applications, as well as analog applications such as CRT modulation.

Maximum Ratings

Emitter (each channel)

Rated Forward Current, DC.....60 mA
Peak Forward Current, DC
(1 µs pulse, 300 pps).....3 A
Power Dissipation at 25°C Ambient .....100 mW
Derate Linearly from 25°C.....1.3 mW/°C

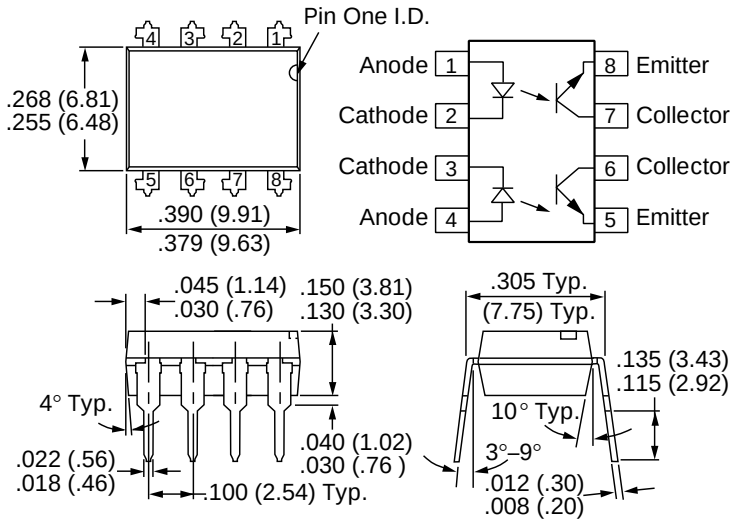
Detector (each channel)

Collector Current .....30 mA
Collector-Emitter Breakdown Voltage.....30 V
Power Dissipation at 25°C Ambient .....150 mW
Derate Linearly from 25°C.....2 mW/°C

Package

Isolation Test Voltage.....5300 VAC_{RMS}
Isolation Resistance
V_{IO}=500 V, T_A=25°C .....$\geq 10^{12}$ Ω
V_{IO}=500 V, T_A=100°C .....$\geq 10^{11}$ Ω
Creepage ..... 7 mm min.
Clearance..... 7 mm min.
Total Package Dissipation
at 25°C Ambient. .....400 mW
Derate Linearly from 25°C.....5.33 mW/°C
Storage Temperature .....–55°C to +150°C
Operating Temperature .....–55°C to +100°C
Lead Soldering Time at 260°C ..... 10 sec.

Dimensions in inches (mm)



Electrical Characteristics (T_A=25°C)

	Symbol	Min.	Typ.	Max.	Unit	Condition
Emitter						
Forward Voltage	V_F		1.25	1.50	V	I_F=20 mA
Reverse Current	I_R		0.1	10	µA	V_R=3.0 V
Junction Capacitance	C_J		25		pF	V_F=0 V
Detector						
Breakdown Voltage, Collector-Emitter Emitter-Collector	BV_{CEO} BV_{ECO}	30 7.0	65 10		V V	I_C=10 µA I_E=10 µA
Leakage Current, Collector -Emitter	I_{CEO}		1.0	100	nA	V_{CE}=10 V
Capacitance						
Collector-Emitter	C_{CE}		8.0		pF	V_{CE}=0 V
Package						
DC Current Transfer Ratio	CTR	20	50		%	I_F=10 mA, V_{CE}=10 V
Saturation Voltage, Collector-Emitter	V_{CEsat}			0.40	V	I_C=2.0 mA, I_F=16 mA
Isolation Capacitance	C_{ISOL}		0.5		pF	f=1.0 MHz
Capacitance between Channels			0.4		pF	f=1.0 MHz
Bandwidth			150		KHz	I_C=2.0 mA, V_{CC}=10 V, R_L= 100 Ω
Switching Times, Output Transistor	t_{on}, t_{off}		3.0		µs	I_C=2 mA, R_E=100 Ω, V_{CE}=10 V

Figure 1. Forward voltage versus forward current

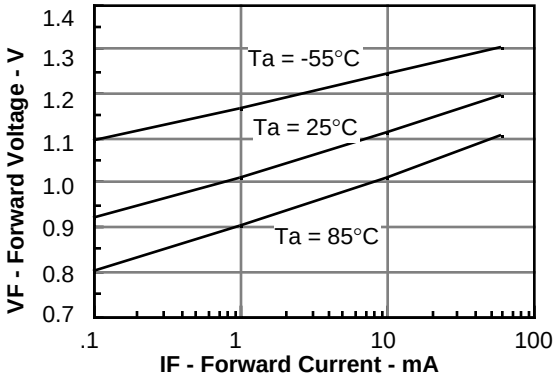


Figure 2. Normalized non-saturated and saturatedCTR at Ta=25°C versus LED current

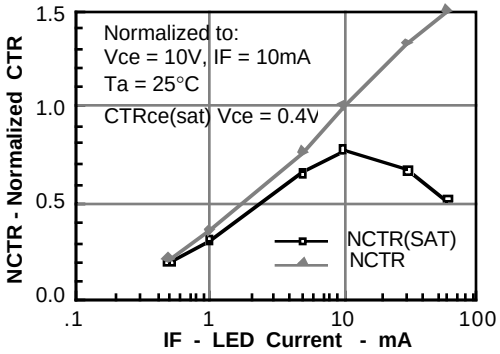


Figure 3. Normalized non-saturated and saturated CTR at Ta=50°C versus LED current

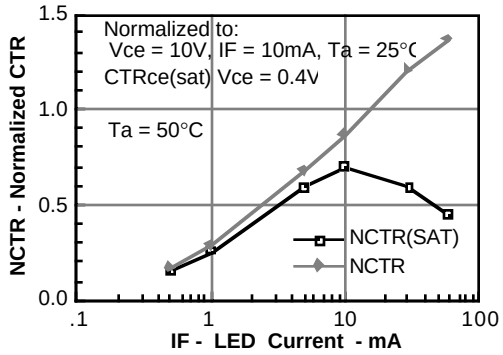


Figure 4. Normalized non-saturated and saturated CTR at Ta=70°C versus LED current

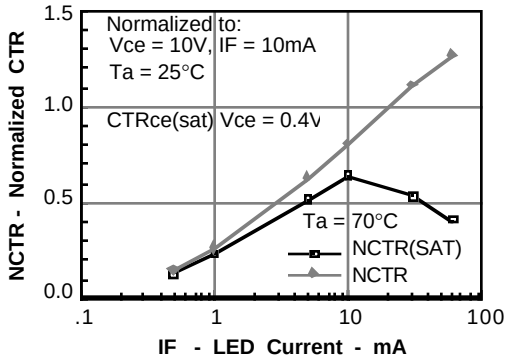


Figure 5. Normalized non-saturated and saturated CTR at Ta=85°C versus LED current

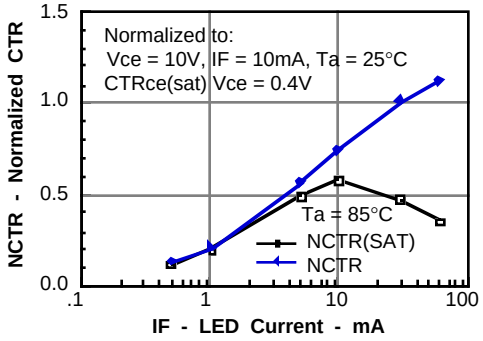


Figure 6. Collector-emitter current versus temperature and LED current

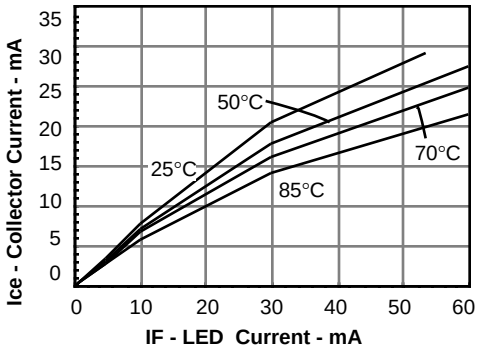


Figure 7. Collector-emitter leakage current versus temperature

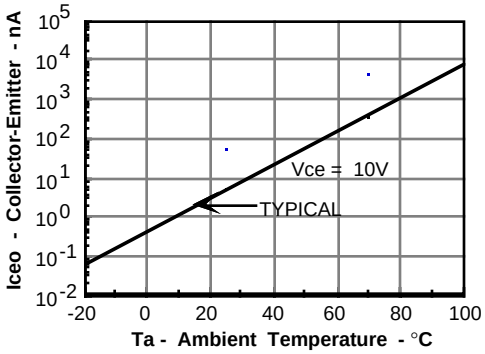


Figure 8. Propagation delay versus collector load resistor

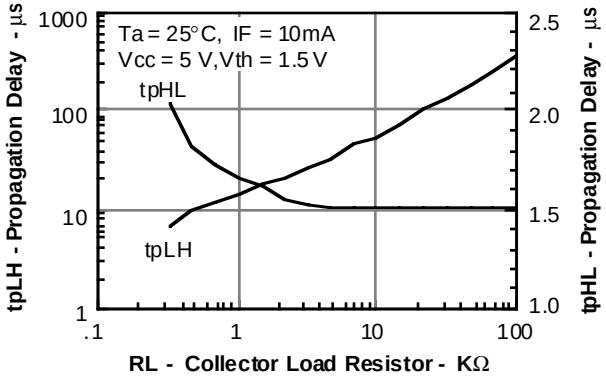


Figure 9. Switching Timing

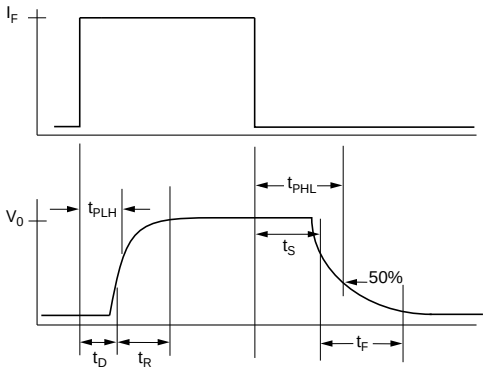


Figure 10. Switching schematic